

2N4402



PNP General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 500 mA.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	40	V
V _{CBO}	Collector-Base Voltage	40	V
V_{EBO}	Emitter-Base Voltage	5.0	V
Ic	Collector Current - Continuous	600	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		2N4402	
P _D	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
R _{eJC}	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

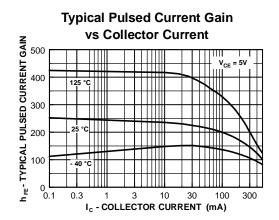
PNP General Purpose Amplifier (continued)

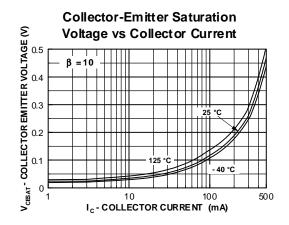
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	40		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 100 \mu\text{A}, I_E = 0$	40		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 100 \mu A, I_C = 0$	5.0		V
I _{CEX}	Collector Cutoff Current	$V_{CE} = 35 \text{ V}, V_{EB} = 0.4 \text{ V}$		0.1	μΑ
I _{BL}	Base Cutoff Current	$V_{CE} = 35 \text{ V}, V_{EB} = 0.4 \text{ V}$		0.1	μΑ
ON CHAF	RACTERISTICS*				
h _{FE}	DC Current Gain	$V_{CE} = 1.0 \text{ V}, I_{C} = 1.0 \text{ mA}$	30		
		$V_{CE} = 1.0 \text{ V}, I_{C} = 10 \text{ mA}$	50		
		$V_{CE} = 2.0 \text{ V}, I_{C} = 150 \text{ mA}$	50 20	150	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$V_{CE} = 2.0 \text{ V}, I_{C} = 500 \text{ mA}$ $I_{C} = 150 \text{ mA}, I_{B} = 15 \text{ mA}$	20	0.40	V
VCE(sat)	Collector-Entitler Saturation Voltage	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.75	V
	Dana Farittan Oatsmatian Valtana				
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$	0.75	0.95	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$	0.75	0.95 1.30	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	, -	0.75		
	Base-Emitter Saturation Voltage	, -	0.75		
SMALL S		, -	0.75		
SMALL S	IGNAL CHARACTERISTICS	I _C = 500 mA, I _B = 50 mA	0.75	1.30	V
SMALL S C _{ob} C _{ib}	SIGNAL CHARACTERISTICS Output Capacitance	$\begin{split} I_{C} &= 500 \text{ mA}, I_{B} = 50 \text{ mA} \\ \\ V_{CB} &= 10 \text{ V}, f = 140 \text{ kHz} \\ \\ V_{EB} &= 0.5 \text{ V}, f = 140 \text{ kHz} \\ \\ I_{C} &= 20 \text{ mA}, V_{CE} = 10 \text{ V}, \end{split}$	1.5	1.30	pF
SMALL S C _{ob} C _{ib}	SIGNAL CHARACTERISTICS Output Capacitance Input Capacitance	I_C = 500 mA, I_B = 50 mA V_{CB} = 10 V, f = 140 kHz V_{EB} = 0.5 V, f = 140 kHz		1.30	pF
SMALL S	SIGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain	I_C = 500 mA, I_B = 50 mA V_{CB} = 10 V, f = 140 kHz V_{EB} = 0.5 V, f = 140 kHz I_C = 20 mA, V_{CE} = 10 V, f = 100 MHz	1.5	8.5 30	v V
SMALL S C _{ob} C _{ib} n _{fe}	SIGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain	$\begin{split} &I_C = 500 \text{ mA}, I_B = 50 \text{ mA} \\ &V_{CB} = 10 \text{ V}, f = 140 \text{ kHz} \\ &V_{EB} = 0.5 \text{ V}, f = 140 \text{ kHz} \\ &I_C = 20 \text{ mA}, V_{CE} = 10 \text{ V}, \\ &f = 100 \text{ MHz} \\ &I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V}, \end{split}$	1.5	8.5 30 250	pF pF
SMALL S Cob Cib hfe hfe hie hre	SIGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Input Impedance	$\begin{split} &I_C = 500 \text{ mA}, I_B = 50 \text{ mA} \\ &V_{CB} = 10 \text{ V}, f = 140 \text{ kHz} \\ &V_{EB} = 0.5 \text{ V}, f = 140 \text{ kHz} \\ &I_C = 20 \text{ mA}, V_{CE} = 10 \text{ V}, \\ &f = 100 \text{ MHz} \\ &I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V}, \end{split}$	1.5 30 0.75	1.30 8.5 30 250 7.5	PF PF kΩ x10 ⁻⁴
SMALL S Cob Cib hfe hie hre hoe	SIGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Input Impedance Voltage Feedback Ratio	$\begin{split} &I_C = 500 \text{ mA}, I_B = 50 \text{ mA} \\ &V_{CB} = 10 \text{ V}, f = 140 \text{ kHz} \\ &V_{EB} = 0.5 \text{ V}, f = 140 \text{ kHz} \\ &I_C = 20 \text{ mA}, V_{CE} = 10 \text{ V}, \\ &f = 100 \text{ MHz} \\ &I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V}, \end{split}$	1.5 30 0.75 0.10	1.30 8.5 30 250 7.5 8.0	PF PF KΩ
SMALL S Cob Cib hfe hfe hie hre hoe	SIGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Input Impedance Voltage Feedback Ratio	$\begin{split} &I_C = 500 \text{ mA}, I_B = 50 \text{ mA} \\ &V_{CB} = 10 \text{ V}, f = 140 \text{ kHz} \\ &V_{EB} = 0.5 \text{ V}, f = 140 \text{ kHz} \\ &I_C = 20 \text{ mA}, V_{CE} = 10 \text{ V}, \\ &f = 100 \text{ MHz} \\ &I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V}, \end{split}$	1.5 30 0.75 0.10	1.30 8.5 30 250 7.5 8.0	PF PF kΩ x10 ⁻⁴
SMALL S Cob Cib hfe hfe hie hre hoe	Output Capacitance Input Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Input Impedance Voltage Feedback Ratio Output Admittance	$\begin{split} &I_C = 500 \text{ mA}, I_B = 50 \text{ mA} \\ &V_{CB} = 10 \text{ V}, f = 140 \text{ kHz} \\ &V_{EB} = 0.5 \text{ V}, f = 140 \text{ kHz} \\ &I_C = 20 \text{ mA}, V_{CE} = 10 \text{ V}, \\ &f = 100 \text{ MHz} \\ &I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V}, \end{split}$	1.5 30 0.75 0.10	1.30 8.5 30 250 7.5 8.0	PF PF kΩ x10 ⁻⁴
SMALL S Cob Cib hfe hie hoe	SIGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Input Impedance Voltage Feedback Ratio Output Admittance NG CHARACTERISTICS	$\begin{split} I_C &= 500 \text{ mA}, \ I_B = 50 \text{ mA} \\ \\ V_{CB} &= 10 \text{ V}, \ f = 140 \text{ kHz} \\ \\ V_{EB} &= 0.5 \text{ V}, \ f = 140 \text{ kHz} \\ \\ I_C &= 20 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 100 \text{ MHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ \\ V_{CC} &= 30 \text{ V}, \ I_C = 150 \text{ mA}, \end{split}$	1.5 30 0.75 0.10	1.30 8.5 30 250 7.5 8.0 100	PF pF kΩ x10 ⁻⁴ μmhos
SMALL S Cob Cib hfe hie hre hoe	SIGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Input Impedance Voltage Feedback Ratio Output Admittance NG CHARACTERISTICS Delay Time	$\begin{split} I_C &= 500 \text{ mA}, \ I_B = 50 \text{ mA} \\ \\ V_{CB} &= 10 \text{ V}, \ f = 140 \text{ kHz} \\ \\ V_{EB} &= 0.5 \text{ V}, \ f = 140 \text{ kHz} \\ \\ I_C &= 20 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 100 \text{ MHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \end{split}$	1.5 30 0.75 0.10	1.30 8.5 30 250 7.5 8.0 100	PF pF kΩ x10 ⁻⁴ μmhos

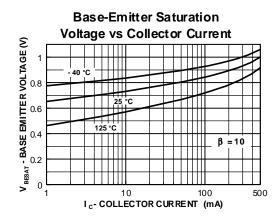
^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

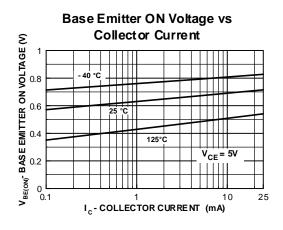
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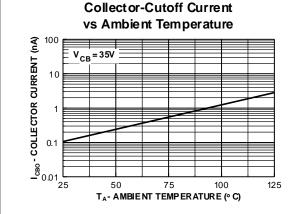
Typical Characteristics

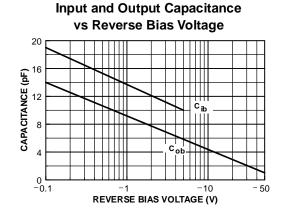






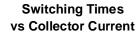


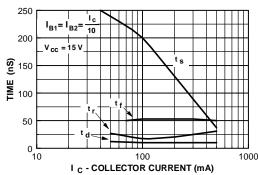




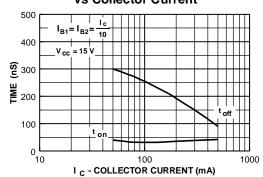
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Typical Characteristics (continued)

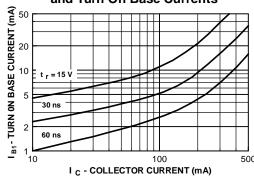




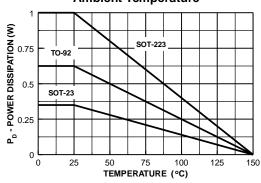
Turn On and Turn Off Times vs Collector Current



Rise Time vs Collector and Turn On Base Currents

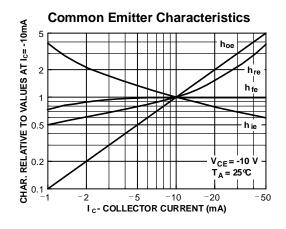


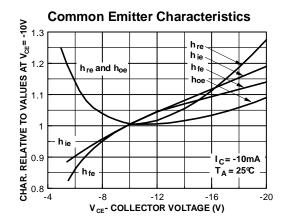
Power Dissipation vs Ambient Temperature

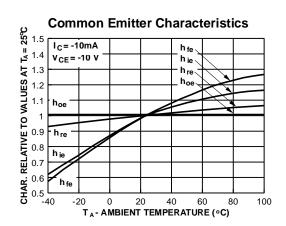


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Typical Common Emitter Characteristics (f = 1.0kHz)







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Test Circuits

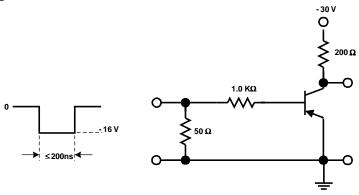


FIGURE 1: Saturated Turn-On Switching Time Test Circuit

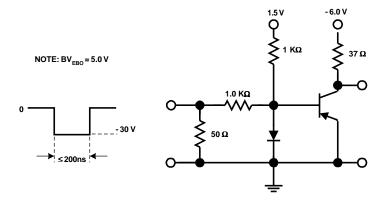


FIGURE 2: Saturated Turn-Off Switching Time Test Circuit

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